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Kind regards,

Team Nexperia

NPN/NPN resistor-equipped transistors;

R1 = 47 kΩ, R2 = 47 kΩ

Rev. 5 — 5 December 2011

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Type number	Package		NPN/PNP		Package
	NXP	JEITA	complement	complement	configuration
PEMH2	SOT666	-	PEMD12	PEMB2	ultra small and flat lead
PUMH2	SOT363	SC-88	PUMD12	PUMB2	very small

Reduces component count

AEC-Q101 qualified

Reduces pick and place costs

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



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1

NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1	001aab555	

3. Ordering information

Table 4. Ord	Table 4. Ordering information					
Type number	Package					
	Name	Description	Version			
PEMH2	-	plastic surface-mounted package; 6 leads	SOT666			
PUMH2	SC-88	plastic surface-mounted package; 6 leads	SOT363			

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
PEMH2	Z2
PUMH2	2*H

[1] * = placeholder for manufacturing site code

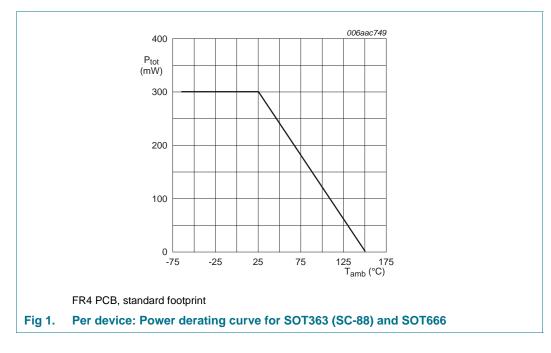
5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-10	V
I _O	output current		-	100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH2 (SOT666)		[1][2] _	200	mW
	PUMH2 (SOT363)		<u>[1]</u> -	200	mW
Per device	9				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMH2 (SOT666)		[1][2] _	300	mW
	PUMH2 (SOT363)		<u>[1]</u> -	300	mW
Т _ј	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



6. Thermal characteristics

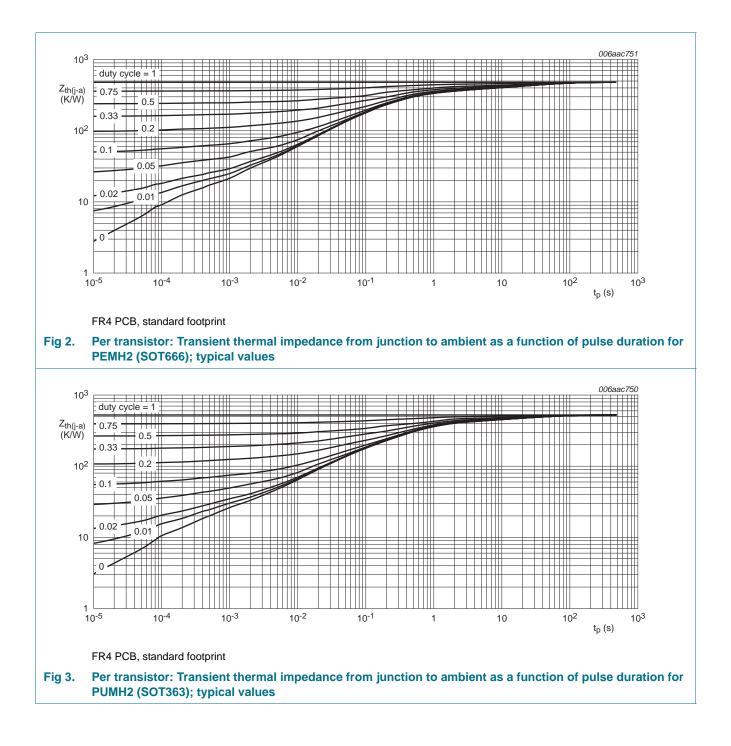
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH2 (SOT666)		<u>[1][2]</u>	-	625	K/W
	PUMH2 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	9					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMH2 (SOT666)		[1][2] _	-	417	K/W
	PUMH2 (SOT363)		<u>[1]</u> _	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMH2; PUMH2

NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



7. Characteristics

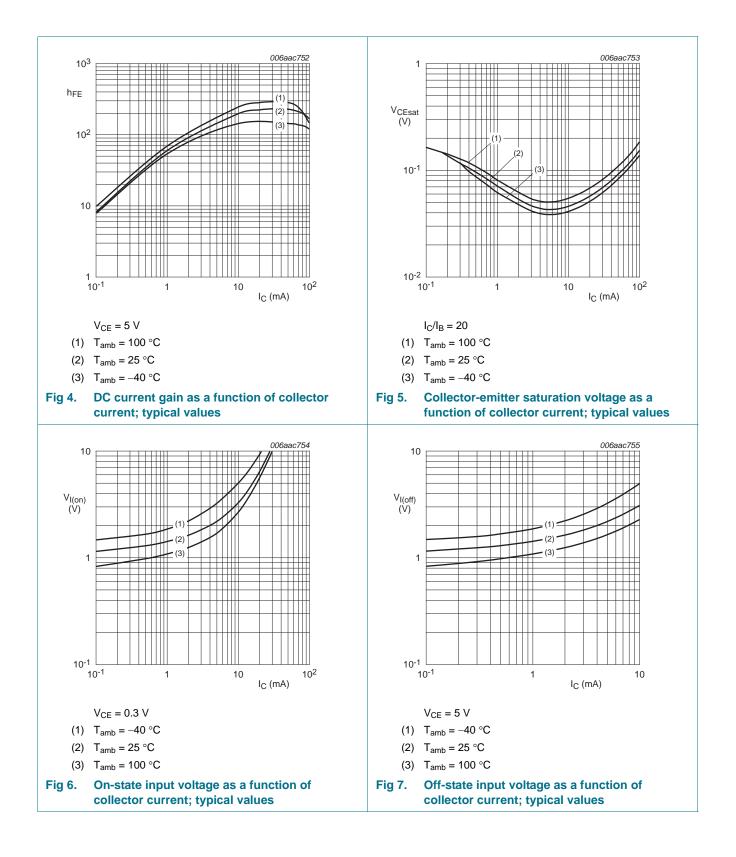
Table 8. $T_{amb} = 2\xi$	Characteristics 5 °C unless otherwise spe	ecified.					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per trans	sistor						
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}$		-	-	1	μA
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	90	μΑ
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 5 mA		80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C}$ = 10 mA; $I_{\rm B}$ = 0.5 mA		-	-	150	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_C = 100 μ A		-	1.2	0.8	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 2 mA		3	1.6	-	V
R1	bias resistor 1 (input)			33	47	61	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C _c	collector capacitance	$\label{eq:V_CB} \begin{array}{l} V_{CB} = 10 \; V; \\ I_E = i_e = 0 \; A; \; f = 1 \; MHz \end{array}$				2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 10 \text{ mA};$ f = 100 MHz	<u>[1]</u>		230		MHz

[1] Characteristics of built-in transistor

PEMH2_PUMH2 Product data sheet

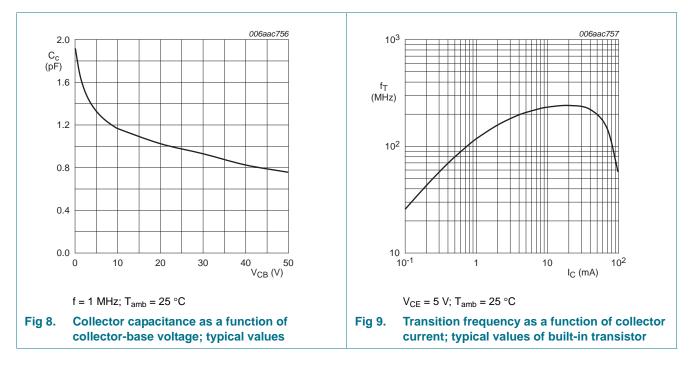
PEMH2; PUMH2

NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



PEMH2; PUMH2

NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

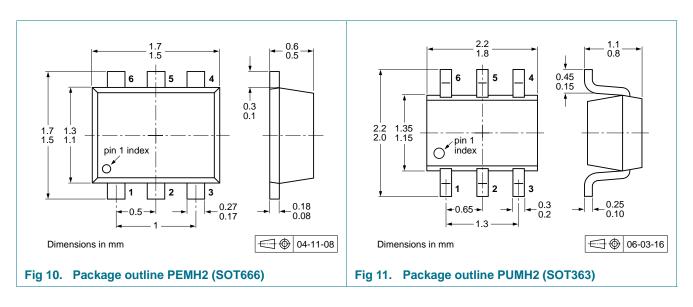


Test information 8.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

Package outline 9.



PEMH2 PUMH2 **Product data sheet**

10. Packing information

Table 9. Packing methods

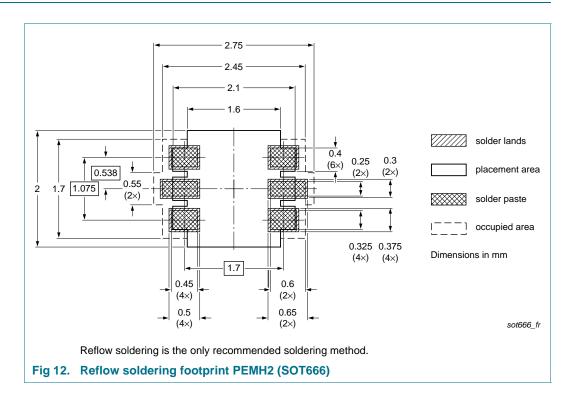
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Туре	Package	Description		Packin	g quant	ity	
number				3000	4000	8000	10000
PEMH2	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMH2	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

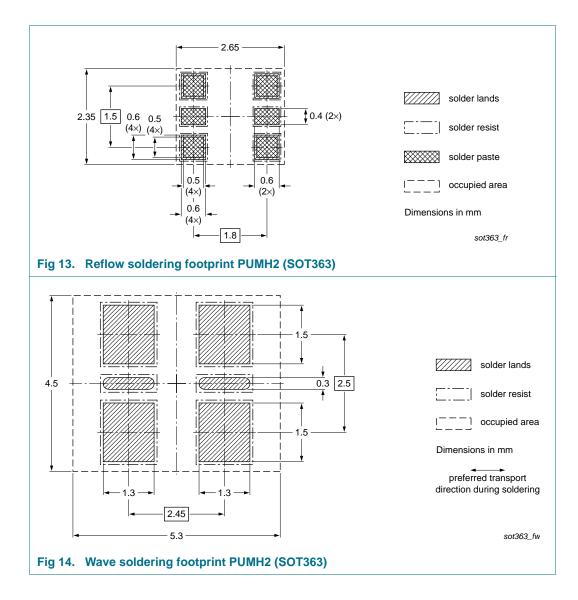
[1] For further information and the availability of packing methods, see Section 14.

- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



PEMH2_PUMH2
Product data sheet

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12. Revision history

ory			
Release date	Data sheet status	Change notice	Supersedes
20111205	Product data sheet	-	PEMH2_PUMH2 v.4
• Table 1 "Proc	duct overview": corrected		
20111116	Product data sheet	-	PEMH2_PUMH2 v.3
20040414	Product data sheet	-	PEMH2_PUMH2 v.2
20031002	Product specification	-	PEMH2 v.1 PUMH2 v.1
20011022	Preliminary specification	-	-
19990803	Product specification	-	-
	Table 1 "Prod 20111205 • Table 1 "Prod 20111116 20040414 20031002 20011022	Release dateData sheet status20111205Product data sheet• Table 1 "Product overview": corrected20111116Product data sheet20040414Product data sheet20031002Product specification20011022Preliminary specification	Release dateData sheet statusChange notice20111205Product data sheet-• Table 1 "Product overview": corrected-20111116Product data sheet-20040414Product data sheet-20031002Product specification-20011022Preliminary specification-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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PEMH2 PUMH2

NPN/NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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